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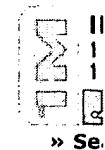
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Chi On Chui; Kim, H.; McIntyre, P.C.; Saraswat, K.C.;
Electron Device Letters, IEEE , Volume: 25 , Issue: 5 , May 2004
Pages:274 - 276

[\[Abstract\]](#) [\[PDF Full-Text \(168 KB\)\]](#) **IEEE JNL****2 Charge trapping in ultrathin hafnium oxide**

Zhu, W.J.; Ma, T.P.; Zafar, S.; Tamagawa, T.;
Electron Device Letters, IEEE , Volume: 23 , Issue: 10 , Oct. 2002
Pages:597 - 599

[\[Abstract\]](#) [\[PDF Full-Text \(201 KB\)\]](#) **IEEE JNL****3 Atomic layer deposition of high-k thin films for gate and capacitor dielectrics**

Senzaki, Y.; Chatham, H.; Park, S.; Bartholomew, L.; Lo, T.; Okuyama, Y.; Ba C.; Tousseau, C.; Fleming, T.; Ford, B.;
Integrated Circuit Design and Technology, 2004. ICICDT '04. International Conference on , 2004
Pages:269 - 274

[\[Abstract\]](#) [\[PDF Full-Text \(582 KB\)\]](#) **IEEE CNF****4 Influence of metal gate materials and processing on planar CMOS device characteristics with high-k gate dielectrics**

Majhi, P.; Young, C.; Bersuker, G.; Wen, H.C.; Brown, G.A.; Foran, B.; Choi, I Zeitzoff, P.M.; Huff, H.R.;
Solid-State Device Research conference, 2004. ESSDERC 2004. Proceeding of